

Silicon NPN Power Transistors

2N5264

DESCRIPTION

- With TO-3 package
- High speed switching
- High reliability

APPLICATIONS

- Switching regulators
- DC-DC convertor
- Solid state relay
- General purpose power amplifiers

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

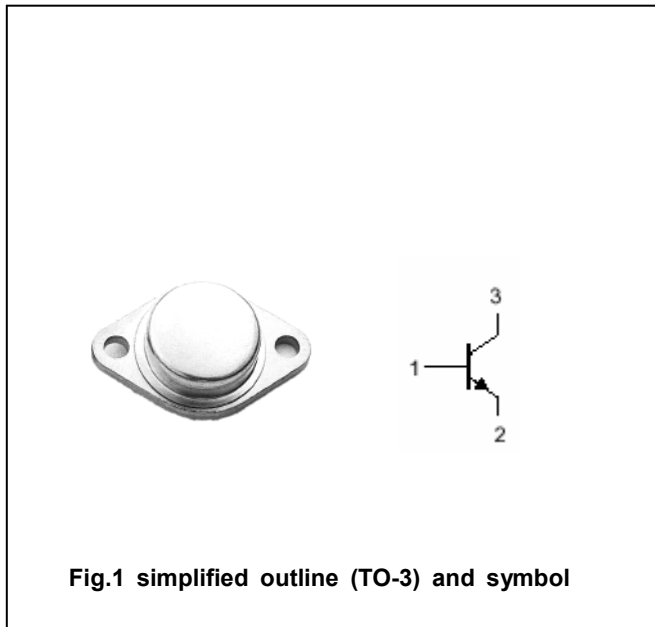


Fig.1 simplified outline (TO-3) and symbol

MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	300	V
V _{CEO}	Collector-emitter voltage	Open base	180	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		7	A
I _B	Base current		2	A
P _T	Total power dissipation	T _c =25°C	87	W
T _j	Junction temperature		165	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.0	°C/W

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	180			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =7A; I _B =1.4A			1.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =7A; I _B =1.4A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =300V; I _E =0			1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	30		300	
f _T	Transition frequency	I _C =1A ; V _{CE} =10V	50			MHz

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PACKAGE OUTLINE

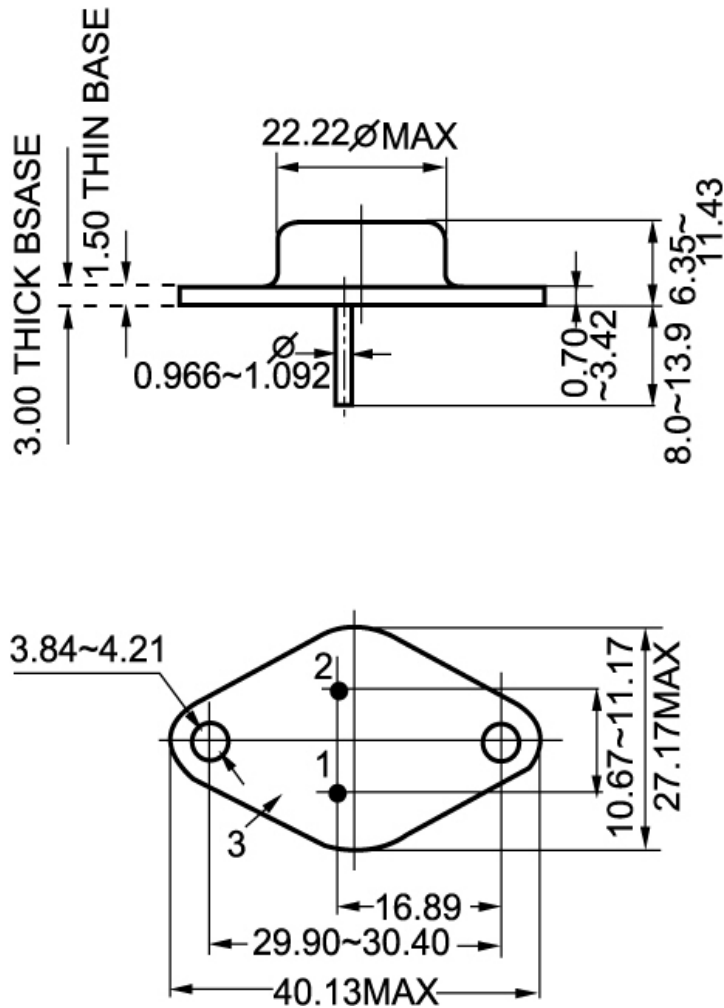


Fig.2 Outline dimensions